



A1C:110S.XX.10

VOLTAGE RATINGS

Part Number	V _{RRM} , VR (V) rep. peak reverse voltage		Max. non-rep. peak reverse voltage T _J = 25 to 150°C
	T _J = 0 to 150°C	T _J = -40 to 0°C	
A1C:110S.02.10	200	200	300
A1C:110S.04.10	400	400	500
A1C:110S.06.10	600	600	700
A1C:110S.08.10	800	800	900
A1C:110S.10.10	1000	1000	1100
A1C:110S.12.10	1200	1200	1300
A1C:110S.14.10	1400	1400	1500
A1C:110S.16.10	1600	1600	1700

This datasheet applies to:

**Metric thread: A1C:110S.XX.10,
A1D:110S.XX.10**

**Inch thread: A2C:110S.XX.10,
A2D:110S.XX.10**

MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
T _J Junction Temperature	-40 to 150	°C	-
T _{stg} Storage Temperature	-40 to 150	°C	-
I _{F(AV)}	Max. Av. current @ Max. T _C	A °C	180° half sine wave
I _{F(RMS)}	Nom. RMS current	A	-
I _{FSM} Max. Peak non-rep. surge current	2.49	kA	50 Hz half cycle sine wave
	2.72		60 Hz half cycle sine wave
	2.84		50 Hz half cycle sine wave
	3.1		60 Hz half cycle sine wave
I ² t Max. I ² t capability	32.22	kA ² s	t = 10ms Initial T _J = 125°C, rated V _{RRM} applied after surge.
	35.12		t = 8.3 ms
	36.73		t = 10ms Initial T _J = 125°C, no voltage applied after surge.
	40.04		t = 8.3 ms
I ² t ^{1/2} Max. I ² t ^{1/2} capability	440	A ² s ^{1/2}	Initial T _J = 125°C, no voltage applied after surge. for time t _x = I ² t ^{1/2} * tx1/2. (0.1 < tx < 10ms).
I _{RRM} Maximum peak reverse current at rated V _{RRM} .	0.5	mA	T _J = 25°C
I _{RM} Peak reverse recovery current	50	A	
di/dt Max. Non-repetitive rate-of-rise current	50	A/μs	T _J = 25°C, V _D = V _{DRM} , I _{FM} = 110A.
F Mounting Force	10	N.m	-



AEGIS

A1C:110S.XX.10

CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_{FM} peak on-state voltage	---	---	1.52	V	Initial $T_J = 25^\circ\text{C}$, 50-60Hz half sine, $I_{peak} = 346\text{A}$.
$V_{F(TO)}$ Threshold voltage	---	---	1.12	V	$T_J = 150^\circ\text{C}$
r_F Slope resistance	---	---	0.9	$\text{m}\Omega$	
t_{rr} Maximum reverse recovery time	---	---	1000	ns	$T_J = 25^\circ\text{C}$, $I_F = 1\text{A}$ to $V_R = 30\text{V}$, $-dI_F/dt = 25\text{A}/\mu\text{s}$
	---	---	2000		$T_J = 25^\circ\text{C}$, $-dI_F/dt = 25\text{A}/\mu\text{s}$, $I_{FM} = \pi \times \text{rated } I_{F(Av.)}$.
R_{thJC} Thermal resistance, junction-to-case	---	---	0.35	$^\circ\text{C}/\text{W}$	DC operation
R_{thCS} Thermal resistance, case-to-sink	---	---	0.08	$^\circ\text{C}/\text{W}$	Mtg. Surface smooth, flat and greased. Single side cooled.
wt Weight	---	100(3.5)	---	g(oz.)	---
Case Style	---	DO-205AA (DO-8)	JEDEC		---

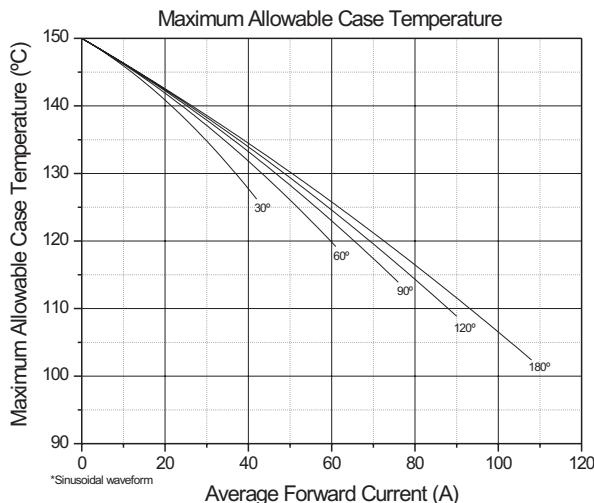


Fig. 1 - Current Ratings Characteristics

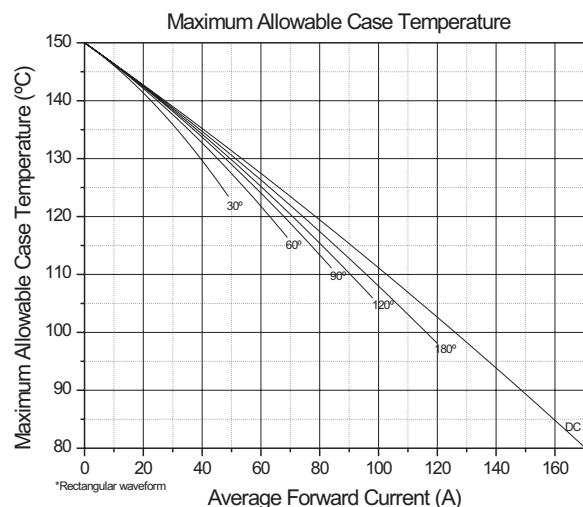


Fig. 2 - Current Ratings Characteristics



Fig. 3 - Forward Power Loss Characteristics

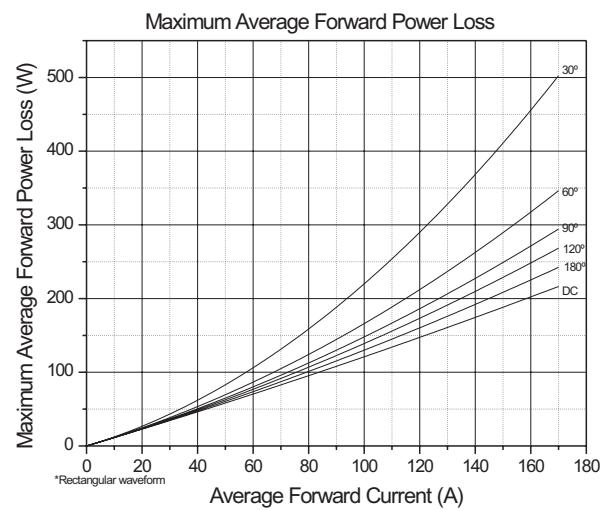


Fig. 4 - Forward Power Loss Characteristics



AEGIS

A1C:110S.XX.10

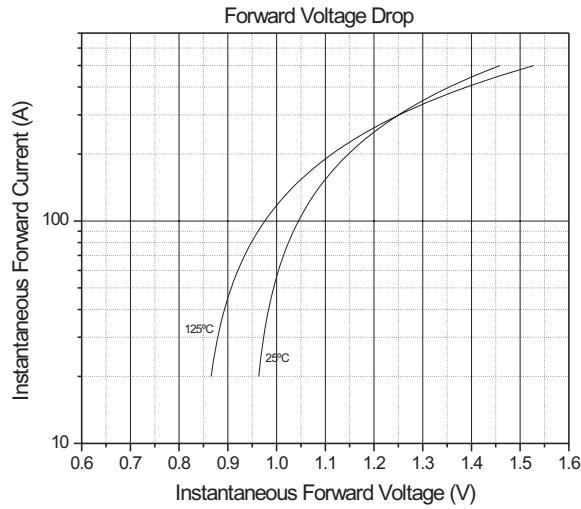


Fig. 5 - Forward Voltage Drop Characteristics

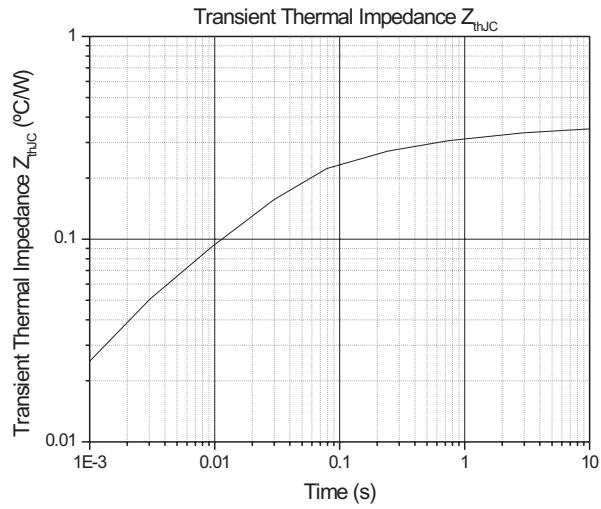


Fig. 6 - Transient Thermal Impedance Characteristics

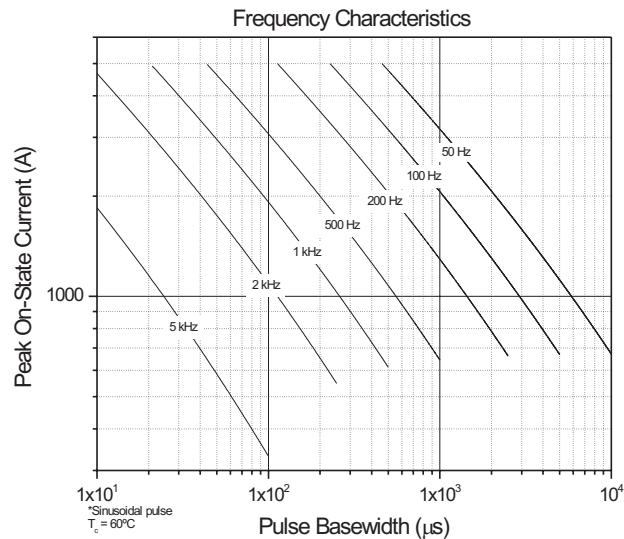


Fig. 7 - Frequency Characteristics

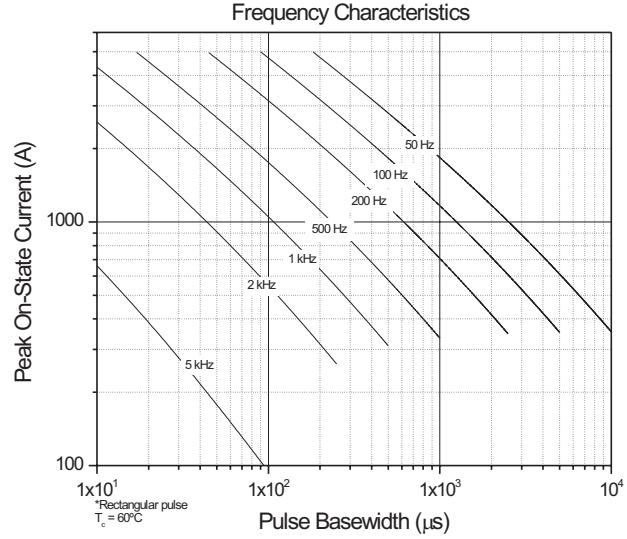


Fig. 8 - Frequency Characteristics

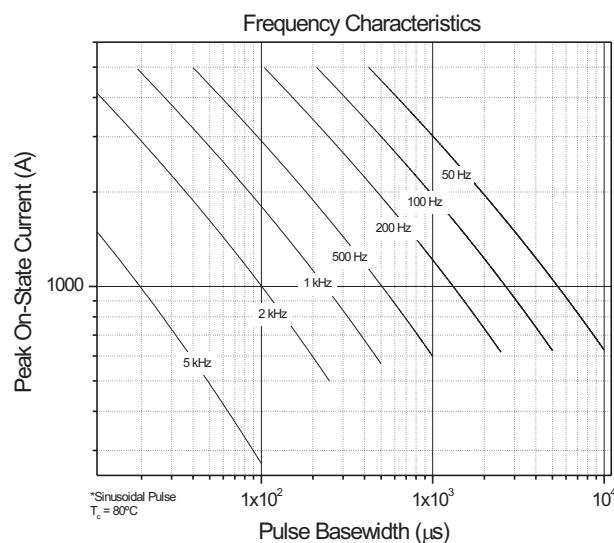


Fig. 9 - Frequency Characteristics

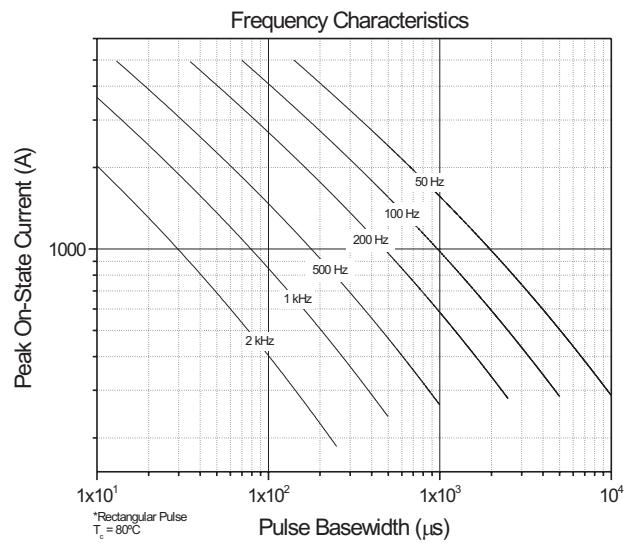


Fig. 10 - Frequency Characteristics



AEGIS

A1C:110S.XX.10

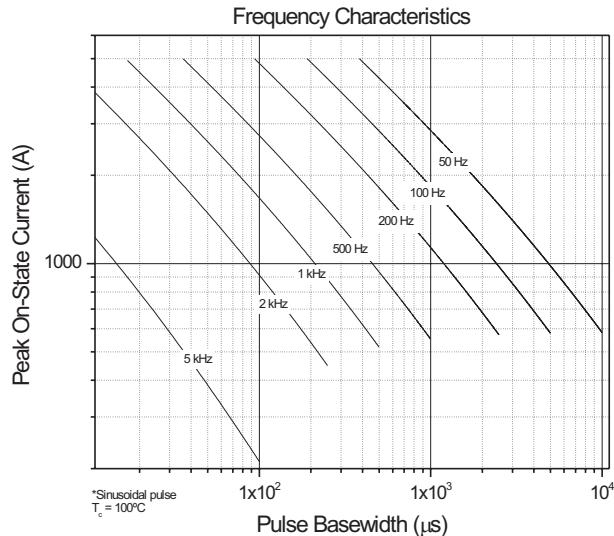


Fig. 11 - Frequency Characteristics

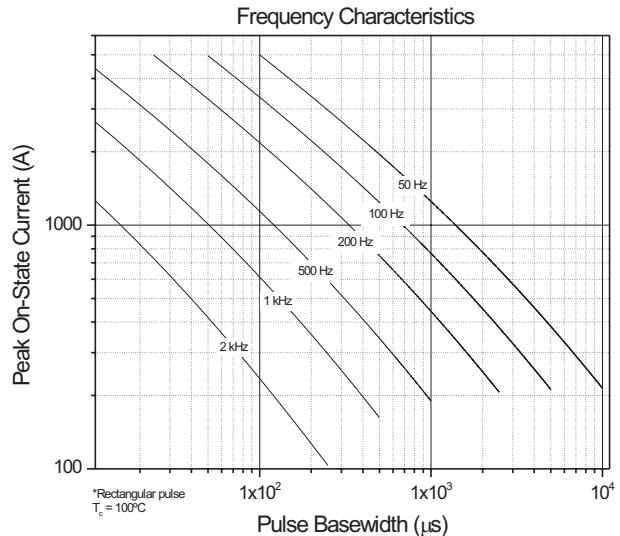


Fig. 12 - Frequency Characteristics

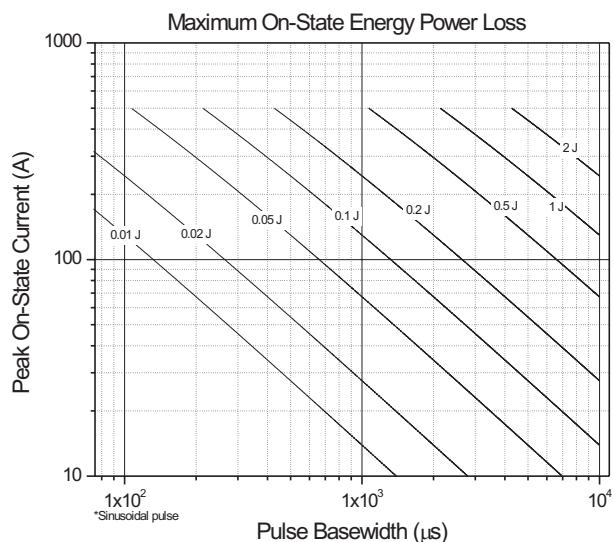


Fig. 13 - Maximum On-State Power Loss Characteristics

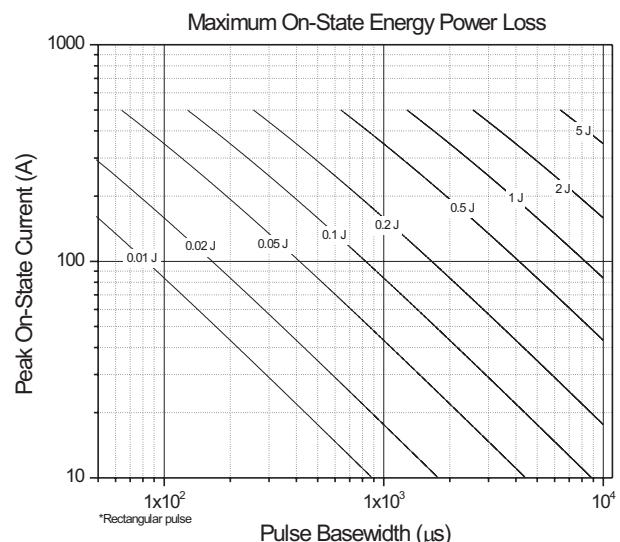


Fig. 14 - Maximum On-State Power Loss Characteristics

DO-205AA (DO-8)

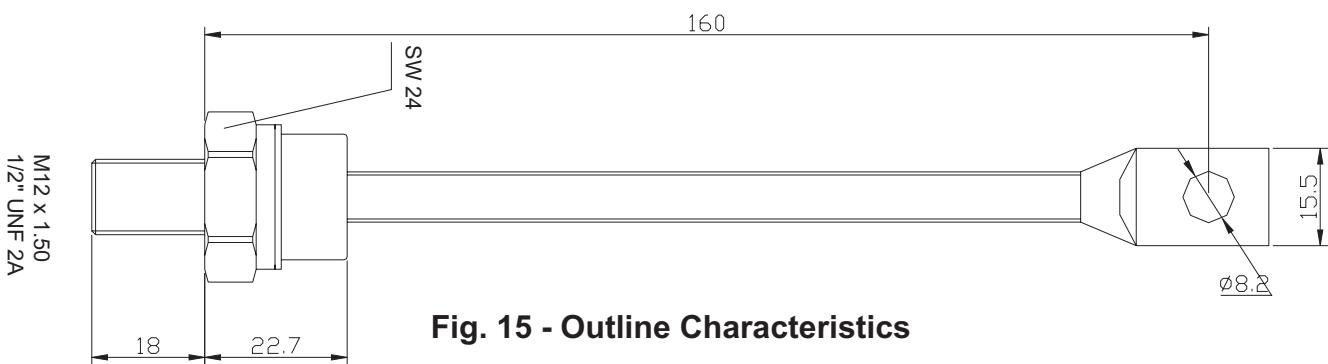


Fig. 15 - Outline Characteristics